

Whang Je Woo

List of Publications by Year in descending order

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papers

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759055

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docs citations

19
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1219
citing authors

#	ARTICLE	IF	CITATIONS
1	MoS ₂ doping by atomic layer deposition of high-k dielectrics using alcohol as process oxidants. Applied Surface Science, 2021, 541, 148504.	3.1	6
2	Atomic-Layer-Deposition-Based 2D Transition Metal Chalcogenides: Synthesis, Modulation, and Applications. Advanced Materials, 2021, 33, e2005907.	11.1	42
3	Interface Defect Engineering of a Large-Scale CVD-Grown MoS ₂ Monolayer via Residual Sodium at the SiO ₂ /Si Substrate. Advanced Materials Interfaces, 2021, 8, 2100428.	1.9	14
4	Interface Defect Engineering of MoS ₂ Monolayer: Interface Defect Engineering of a Large-Scale CVD-Grown MoS ₂ Monolayer via Residual Sodium at the SiO ₂ /Si Substrate (Adv. Mater. Interfaces 14/2021). Advanced Materials Interfaces, 2021, 8, 2170080.	1.9	1
5	Reaction Mechanisms of Non-hydrolytic Atomic Layer Deposition of Al ₂ O ₃ with a Series of Alcohol Oxidants. Journal of Physical Chemistry C, 2021, 125, 18151-18160.	1.5	6
6	Self-Powered Gas Sensors: 2D Transition Metal Dichalcogenide Heterostructures for p- and n-Type Photovoltaic Self-Powered Gas Sensor (Adv. Funct. Mater. 43/2020). Advanced Functional Materials, 2020, 30, 2070284.	7.8	1
7	2D Transition Metal Dichalcogenide Heterostructures for p- and n-Type Photovoltaic Self-Powered Gas Sensor. Advanced Functional Materials, 2020, 30, 2003360.	7.8	102
8	Synthesis of two-dimensional MoS ₂ /graphene heterostructure by atomic layer deposition using MoF ₆ precursor. Applied Surface Science, 2019, 494, 591-599.	3.1	25
9	Bi-layer high- <i>k</i> dielectrics of Al ₂ O ₃ /ZrO ₂ to reduce damage to MoS ₂ channel layers during atomic layer deposition. 2D Materials, 2019, 6, 015019.	2.0	12
10	High-Performance Ink-Synthesized Cu-Gate Thin-Film Transistor with Diffusion Barrier Formation. Metals and Materials International, 2018, 24, 652-656.	1.8	1
11	Enhanced Light Stability of InGaZnO Thin-Film Transistors by Atomic-Layer-Deposited Y ₂ O ₃ with Ozone. ACS Applied Materials & Interfaces, 2018, 10, 2143-2150.	4.0	41
12	High-Performance Gas Sensor Using a Large-Area WS ₂ /Se ₂ Alloy for Low-Power Operation Wearable Applications. ACS Applied Materials & Interfaces, 2018, 10, 34163-34171.	4.0	93
13	Recovery Improvement for Large-Area Tungsten Diselenide Gas Sensors. ACS Applied Materials & Interfaces, 2018, 10, 23910-23917.	4.0	115
14	Low-temperature synthesis of 2D MoS ₂ on a plastic substrate for a flexible gas sensor. Nanoscale, 2018, 10, 9338-9345.	2.8	142
15	Highly stable 2D material (2DM) field-effect transistors (FETs) with wafer-scale multidyad encapsulation. Nanotechnology, 2017, 28, 055203.	1.3	1
16	Catalytic chemical vapor deposition of large-area uniform two-dimensional molybdenum disulfide using sodium chloride. Nanotechnology, 2017, 28, 465103.	1.3	42
17	Self-Limiting Layer Synthesis of Transition Metal Dichalcogenides. Scientific Reports, 2016, 6, 18754.	1.6	74
18	Effects of TaN Diffusion Barrier on Cu-Gate ZnO:N Thin-Film Transistors. IEEE Electron Device Letters, 2016, 37, 599-602.	2.2	4

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19	Effect of Al ₂ O ₃ Deposition on Performance of Top-Gated Monolayer MoS ₂ -Based Field Effect Transistor. ACS Applied Materials & Interfaces, 2016, 8, 28130-28135.	4.0	40